MMG50S060B6R

600V 50A IGBT Module

February 2015 **Version 01** **RoHS Compliant**

PRODUCT FEATURES

☐ IGBT CHIP(600V NPT technology)

☐ Low switching losses

☐ $V_{CE(sat)}$ with positive temperature coefficient

☐ Fast switching and short tail current

☐ Free wheeling diodes with fast and Low Erec

APPLICATIONS

☐ AC motor control

☐ Motion/servo control

☐ Inverter and power supplies

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃	600	V
V_{GES}	Gate Emitter Voltage		±20	
I_C	DC Collector Current	T_C=25℃	70	A
		T_C=70℃	50	
I_{CM}	Repetitive Peak Collector Current	tp=1ms	100	
P_{tot}	Power Dissipation Per IGBT		200	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	T_J=25℃	600	V
$I_{F(AV)}$	Average Forward Current	T_C=25℃	50	A
I_{FRM}	Repetitive Peak Forward Current	tp=1ms	100	
I^2t		T_J=125℃, t=10ms, V_R=0V	240	A^2S

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IGBT-inverter
ELECTRICAL CHARACTERISTICS

T_C =25°C unless otherwise specified

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=0.9mA		4.2	4.8	5.4	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=50A, V_{GE}=15V, T_J=25℃			1.95	2.25	
		I_C=50A, V_{GE}=15V, T_J=125℃			2.25		
I_{CES}	Collector Leakage Current	V_{CE}=600V, V_{GE}=0V, T_J=25℃				100	μA
		V_{CE}=600V, V_{GE}=0V, T_J=125℃				1	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±15V, T_J=125℃		-400		400	nA
R_{gint}	Integrated Gate Resistor				0		Ω
Q_g	Gate Charge	V_{CE}=300V, I_C=50A , V_{GE}=15V			0.25		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			3		nF
C_{res}	Reverse Transfer Capacitance				80		pF
$t_{d(on)}$	Turn on Delay Time	V_{CC}=300V,I_C=50A R_G =20Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		50		ns
			T_J=125℃		60		ns
t_r	Rise Time		T_J=25℃		45		ns
			T_J=125℃		50		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=300V,I_C=50A R_G =20Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		230		ns
			T_J=125℃		270		ns
t_f	Fall Time		T_J=25℃		40		ns
			T_J=125℃		45		ns
E_{on}	Turn on Energy	V_{CC}=300V,I_C=50A R_G =20Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		0.5		mJ
			T_J=125℃		0.7		mJ
E_{off}	Turn off Energy		T_J=25℃		0.9		mJ
			T_J=125℃		1.2		mJ
I_{SC}	Short Circuit Current	tpsc≤10μS , V_{GE}=15V T_J=125℃,V_{CC}=360V			200		A
R_{thJC}	Junction to Case Thermal Resistance （Per IGBT）					0.6	K /W

Diode-inverter
ELECTRICAL CHARACTERISTICS

T_C =25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=50A , V_{GE}=0V, T_J=25℃		1.65	1.95	V
		I_F=50A , V_{GE}=0V, T_J=125℃		1.6		
t_{rr}	Reverse Recovery Time	I_F=50A , V_R=300V dI_F/dt=-850A/μs T_J =125℃		195		ns
I_{RRM}	Max. Reverse Recovery Current			37		A
Q_{RR}	Reverse Recovery Charge			4.2		μC
E_{rec}	Reverse Recovery Energy			0.76		mJ
R_{thJCD}	Junction to Case Thermal Resistance （Per Diode）				1.25	K /W

MODULE CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		150	℃
T_{Jop}	Operating Temperature		-40~125	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		> 200	
Torque	to heatsink	Recommended（M6）	3~5	Nm
	to terminal	Recommended（M5）	2.5~5	Nm
Weight			160	g

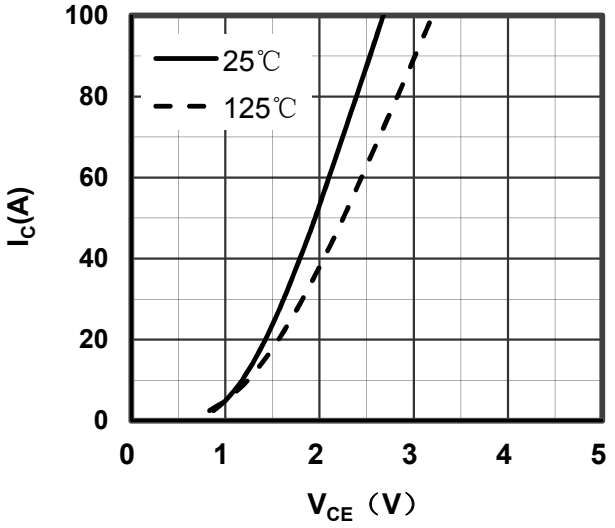


Figure 1. Typical Output Characteristics IGBT-inverter

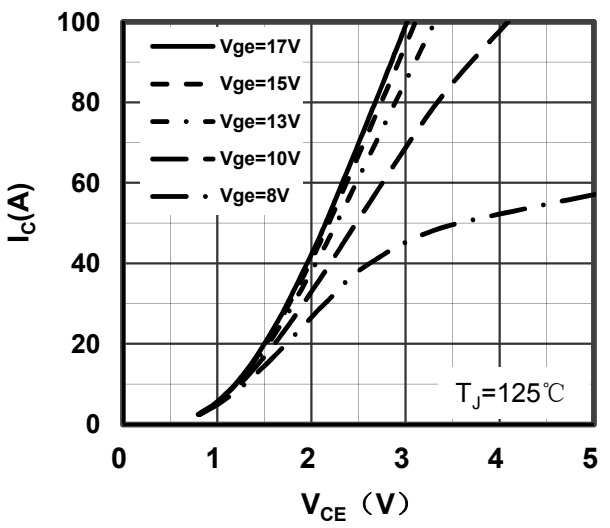


Figure 2. Typical Output Characteristics IGBT-inverter

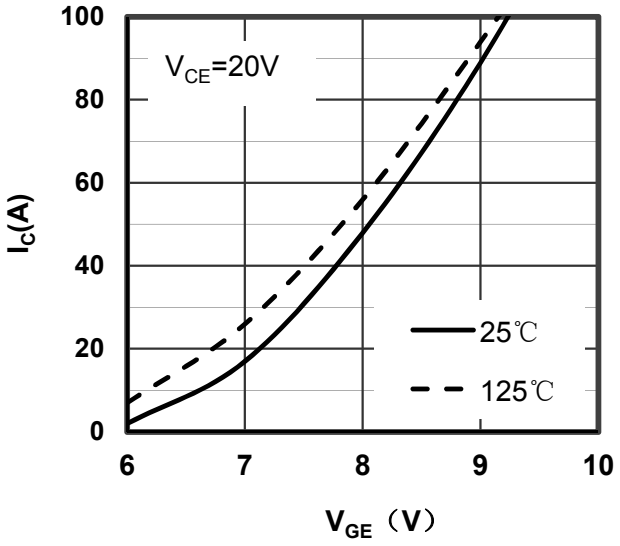


Figure 3. Typical Transfer characteristics IGBT-inverter

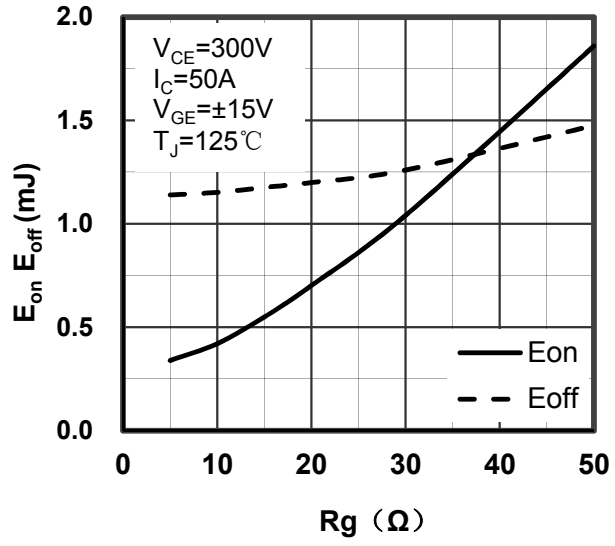


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

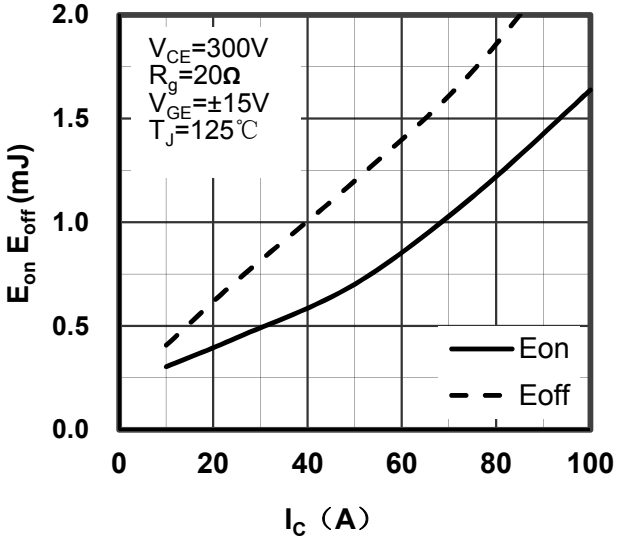


Figure 5. Switching Energy vs Collector Current IGBT-inverter

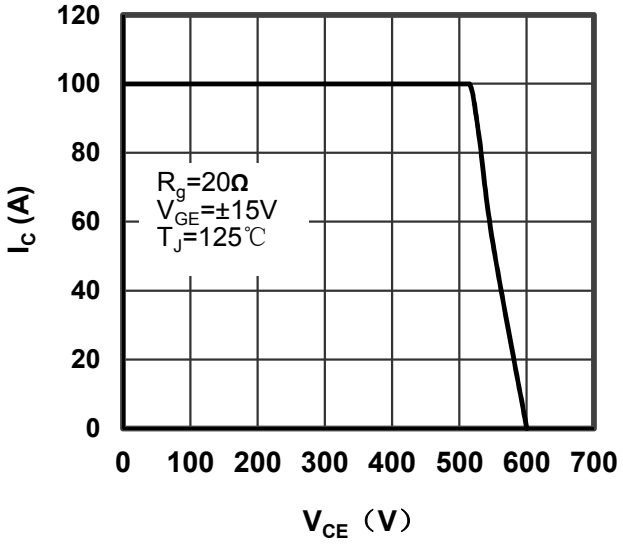


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

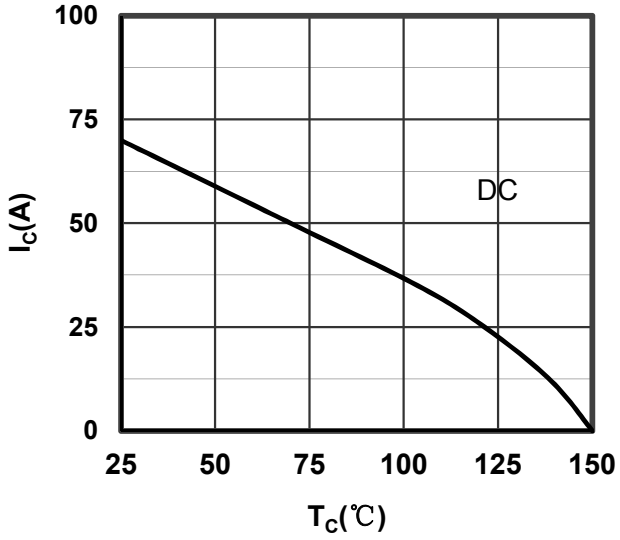


Figure 7. Collector Current vs Case temperature IGBT -inverter

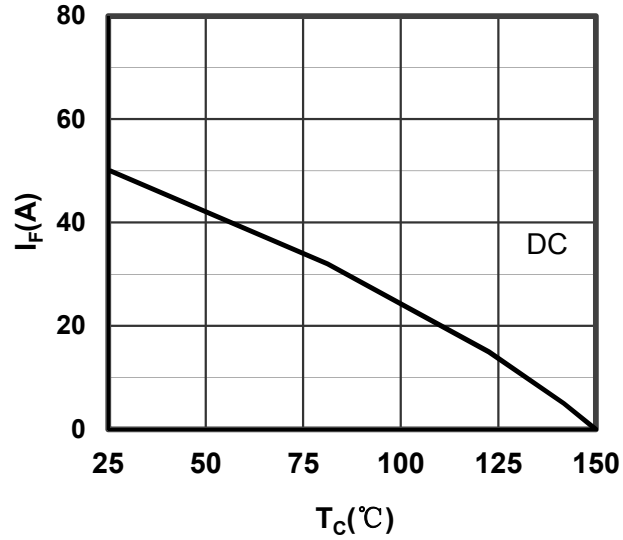


Figure 8. Forward current vs Case temperature Diode -inverter

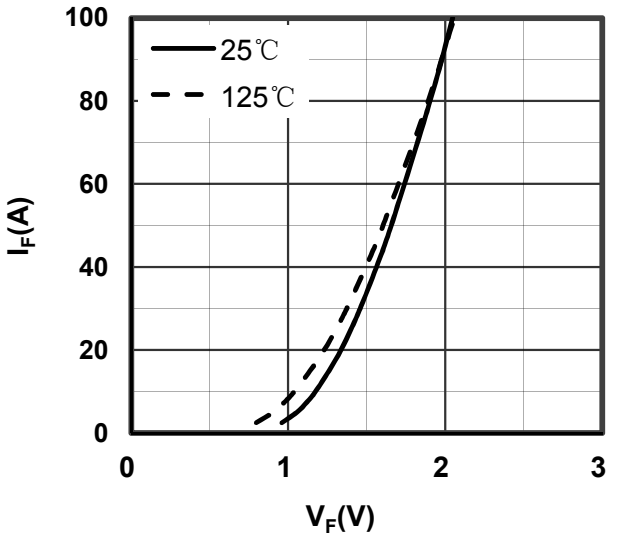


Figure 9. Diode Forward Characteristics Diode -inverter

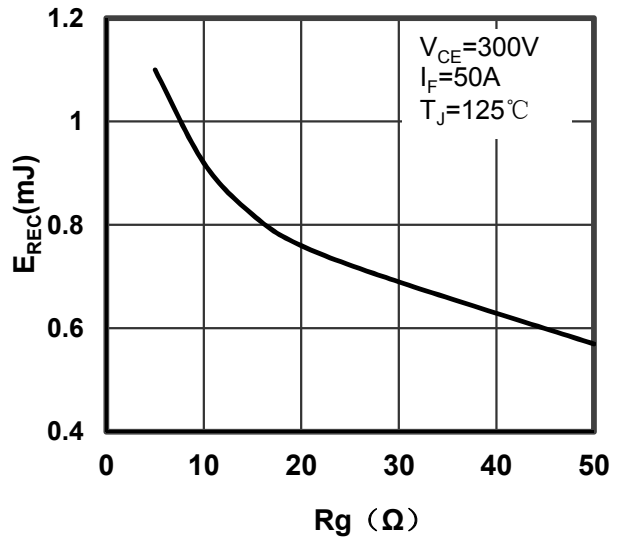


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

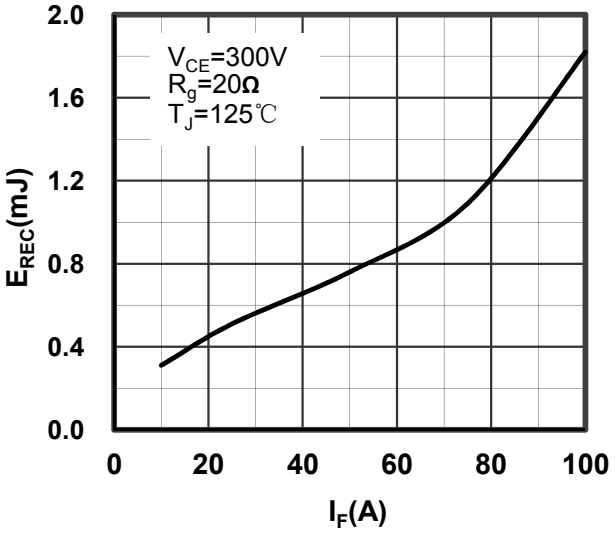


Figure 11. Switching Energy vs Forward Current Diode-inverter

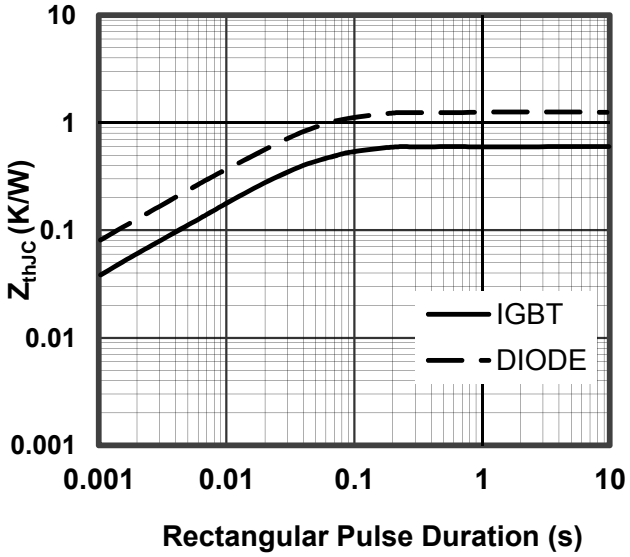


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

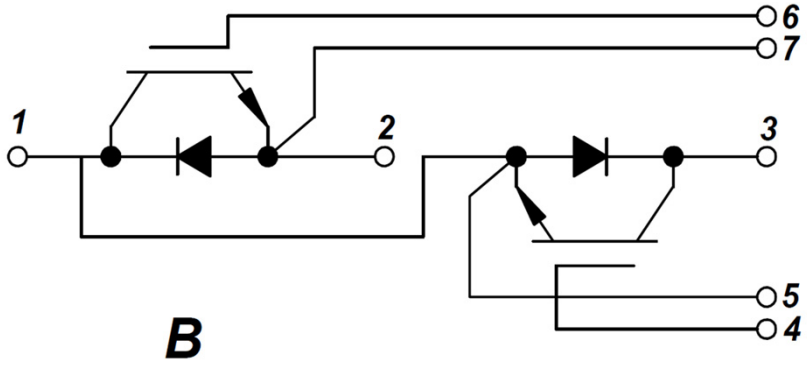
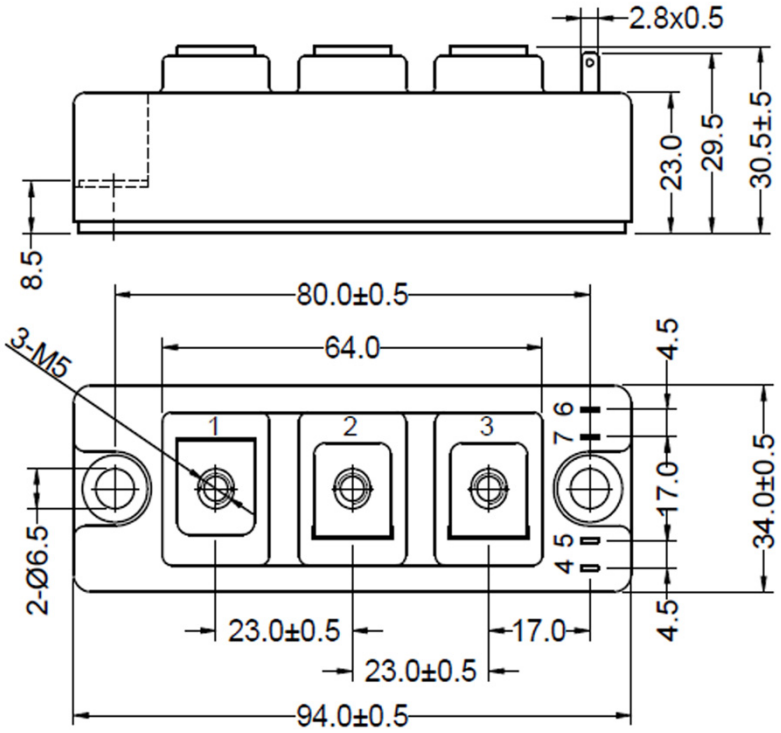


Figure 13. Circuit Diagram



Dimensions in (mm)

Figure 14. Package Outline